N- and P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY			
	V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
N-Channel	20	0.0145 at V_{GS} = 10 V	9.6
		0.017 at V_{GS} = 4.5 V	8.6
P-Channel	- 20	0.033 at V_{GS} = - 4.5 V	- 6.2
		0.050 at V_{GS} = - 2.5 V	- 5

FEATURES

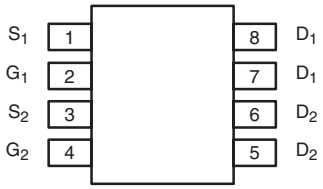
- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- Compliant to RoHS directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

APPLICATIONS

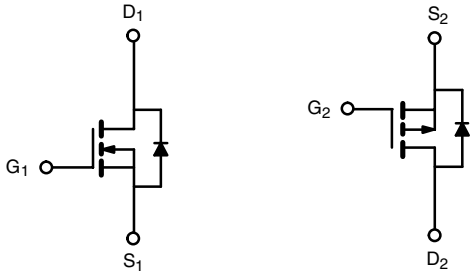
- Level Shift
- Load Switch

SO-8



Top View

Ordering Information: Si4511DY-T1-E3 (Lead (Pb)-free)
Si4511DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted							
Parameter		Symbol	N-Channel		P-Channel		Unit
			10 s	Steady State	10 s	Steady State	
Drain-Source Voltage		V_{DS}	20		- 20		V
Gate-Source Voltage		V_{GS}	± 16		± 12		
Continuous Drain Current (T_J = 150 °C)[a, b]	T_A = 25 °C	I_D	9.6	7.2	- 6.2	- 4.6	A
	T_A = 70 °C		7.7	5.8	- 4.9	- 3.7	
Pulsed Drain Current		I_{DM}	40		- 40		
Continuous Source Current (Diode Conduction)[a]		I_S	1.7	0.9	- 1.7	- 0.9	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	2	1.1	2	1.1	W
	T_A = 70 °C		1.3	0.7	1.3	0.7	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150				°C

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	N-Channel		P-Channel		Unit
			Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient[a]	t ≤ 10 s	R_{thJA}	50	62.5	50	62.5	°C/W
	Steady State		85	110	90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	30	40	30	35	

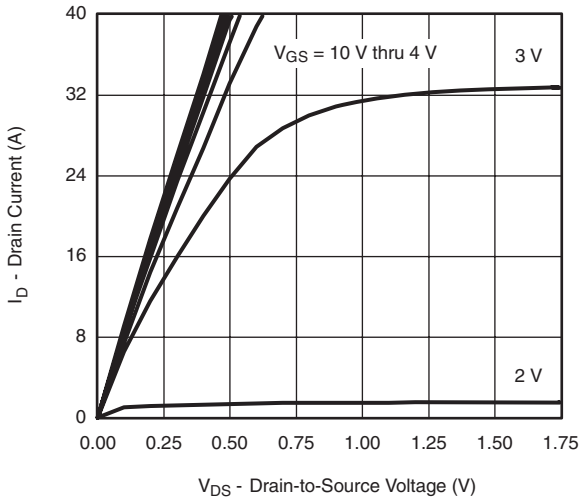
Notes:
a. Surface Mounted on 1" x 1" FR4 board.
b. t ≤ 10 s.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted							
Parameter	**Symbol**	**Test Conditions**		**Min.**	**Typ.**	**Max.**	**Unit**
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250 µA	N-Ch	0.6		1.8	V
		$V_{DS} = V_{GS}$, I_D = - 250 µA	P-Ch	- 0.6		- 1.4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 16 V	N-Ch			± 100	nA
		V_{DS} = 0 V, V_{GS} = ± 12 V	P-Ch			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V	N-Ch			1	µA
		V_{DS} = - 20 V, V_{GS} = 0 V	P-Ch			- 1	
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 55 °C	N-Ch			5	
		V_{DS} = - 20 V, V_{GS} = 0 V, T_J = 55 °C	P-Ch			- 5	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	N-Ch	40			A
		V_{DS} = - 5 V, V_{GS} = - 4.5 V	P-Ch	- 40			
Drain-Source On-State Resistance[b]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 9.6 A	N-Ch		0.0115	0.0145	Ω
		V_{GS} = - 4.5 V, I_D = - 6.2 A	P-Ch		0.022	0.033	
		V_{GS} = 4.5 V, I_D = 8.6 A	N-Ch		0.0135	0.017	
		V_{GS} = - 2.5 V, I_D = - 5 A	P-Ch		0.035	0.050	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 9.6 A	N-Ch		33		S
		V_{DS} = - 15 V, I_D = - 6.2 A	P-Ch		17		
Diode Forward Voltag[b]	V_{SD}	I_S = 1.7 A, V_{GS} = 0 V	N-Ch		0.8	1.2	V
		I_S = - 1.7 A, V_{GS} = 0 V	P-Ch		- 0.8	- 1.2	
Dynamic[a]							
Total Gate Charge	Q_g	N-Channel V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 9.6 A P-Channel V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_D = - 6.2 A	N-Ch		11.5	18	nC
			P-Ch		17	20	
Gate-Source Charge	Q_{gs}		N-Ch		3.7		
			P-Ch		4.1		
Gate-Drain Charge	Q_{gd}		N-Ch		3.3		
			P-Ch		4.3		
Turn-On Delay Time	$t_{d(on)}$	N-Channel V_{DD} = 10 V, R_L = 10 Ω $I_D \cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω P-Channel V_{DD} = - 10 V, R_L = 10 Ω $I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω	N-Ch		12	20	ns
			P-Ch		25	40	
Rise Time	t_r		N-Ch		12	20	
			P-Ch		30	45	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch		55	85	
			P-Ch		70	105	
Fall Time	t_f		N-Ch		15	25	
			P-Ch		50	75	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 1.7 A, dI/dt = 100 A/µs	N-Ch		50	100	
		I_F = - 1.7 A, dI/dt = 100 A/µs	P-Ch		40	80	

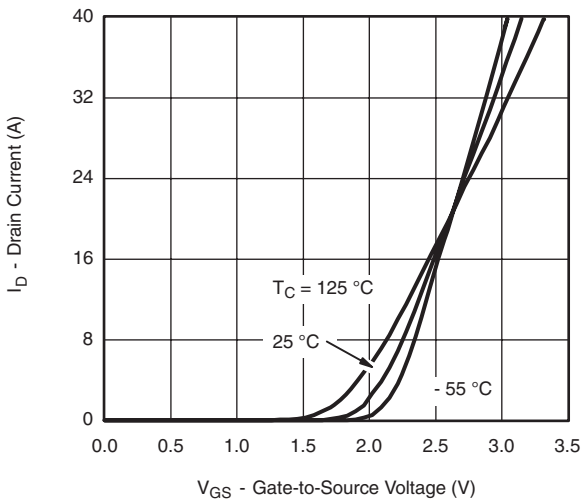
Notes:
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

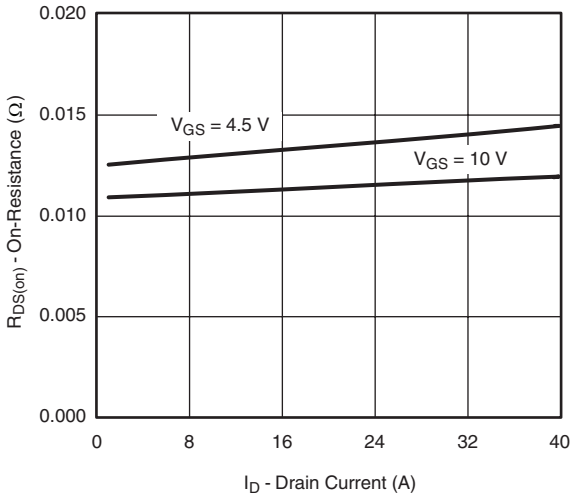
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



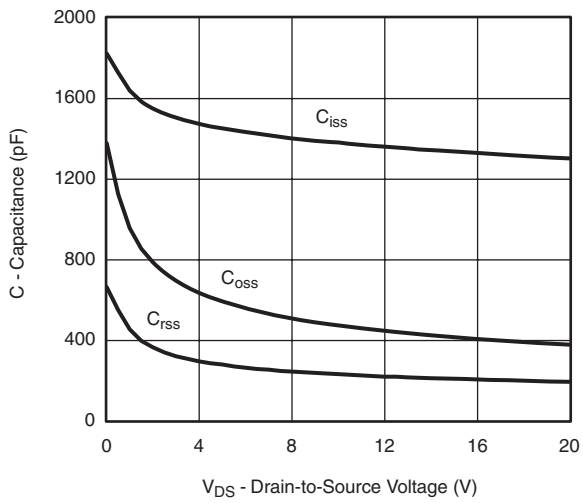
Output Characteristics



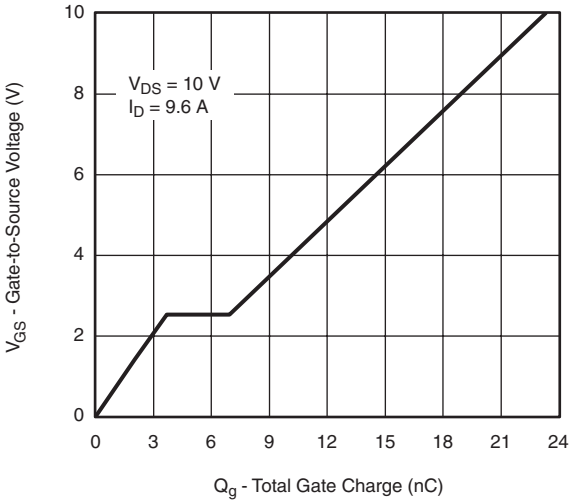
Transfer Characteristics



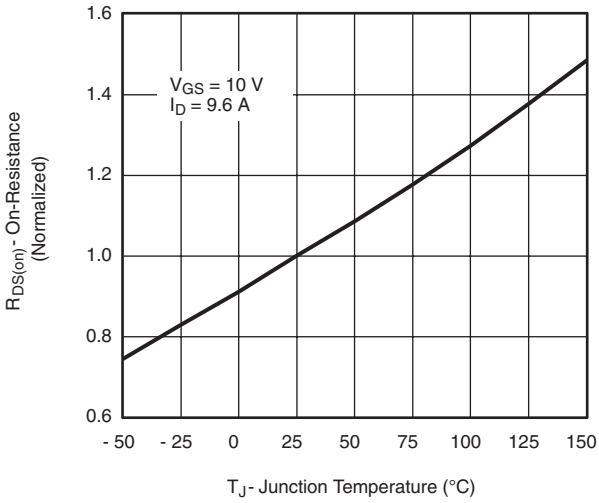
On-Resistance vs. Drain Current



Capacitance

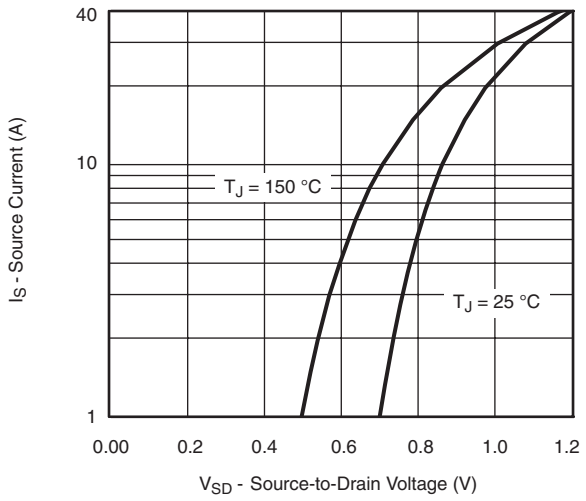


Gate Charge

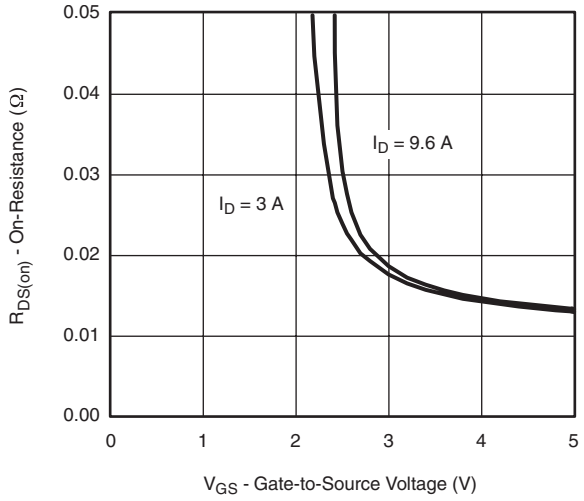


On-Resistance vs. Junction Temperature

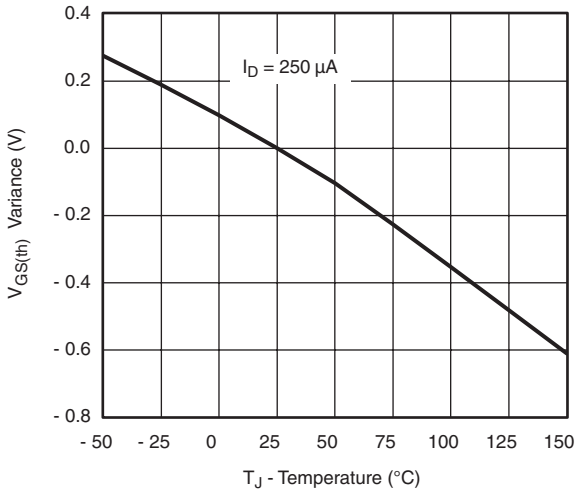
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



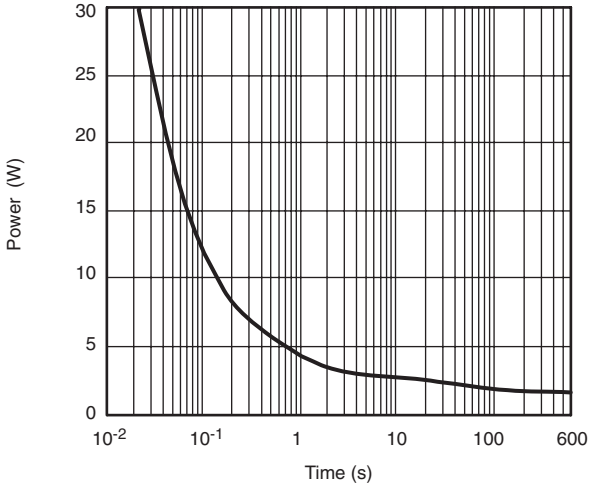
Source-Drain Diode Forward Voltage



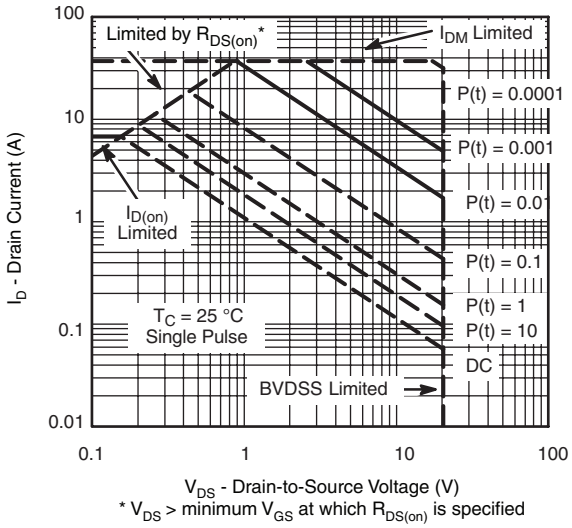
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



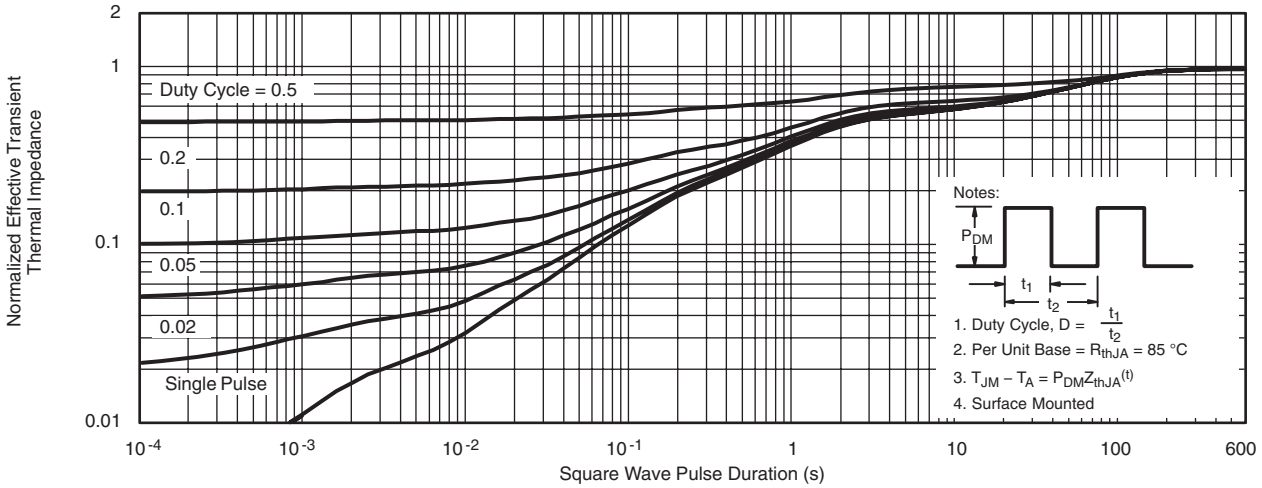
Single Pulse Power



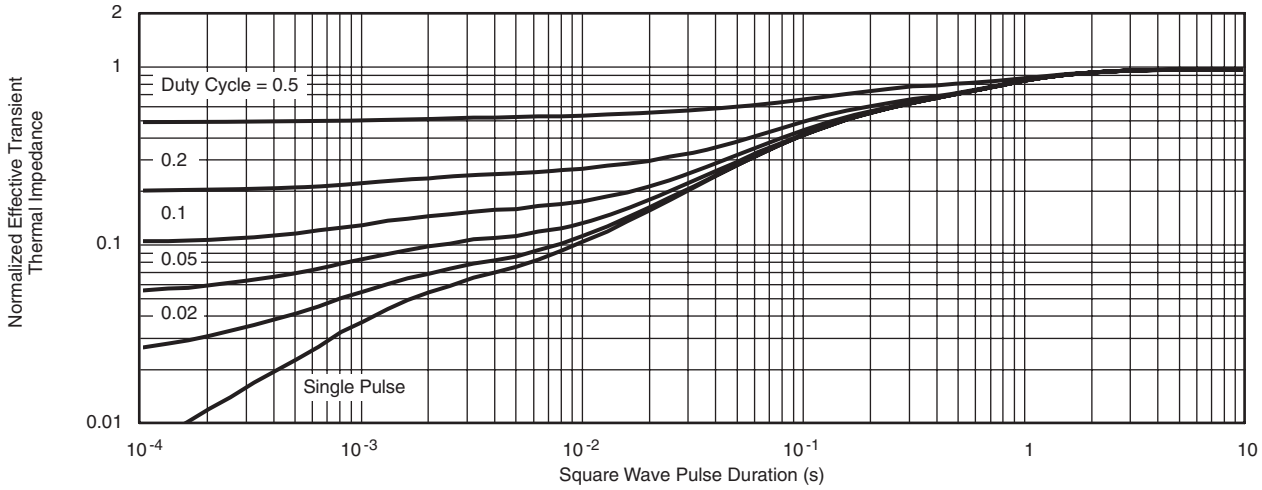
* V_{DS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

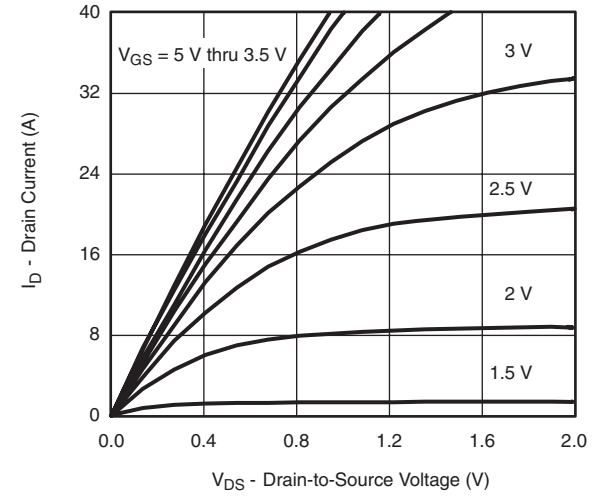


Normalized Thermal Transient Impedance, Junction-to-Ambient

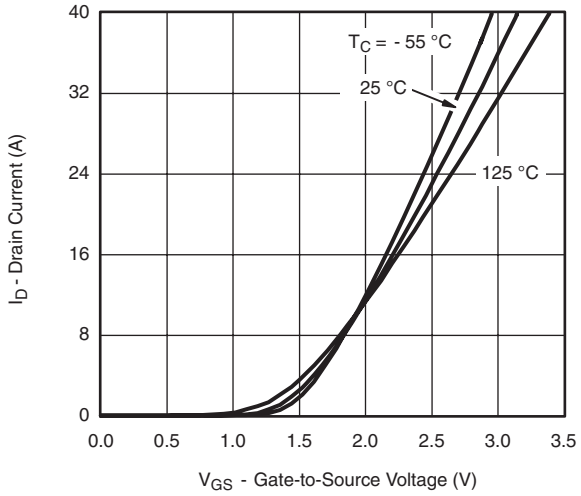


Normalized Thermal Transient Impedance, Junction-to-Foot

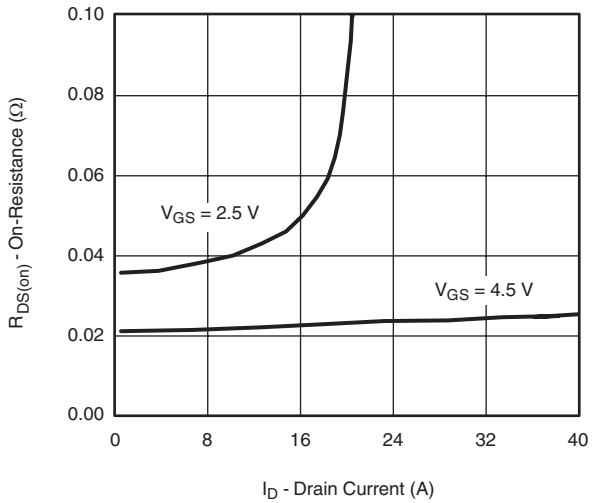
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



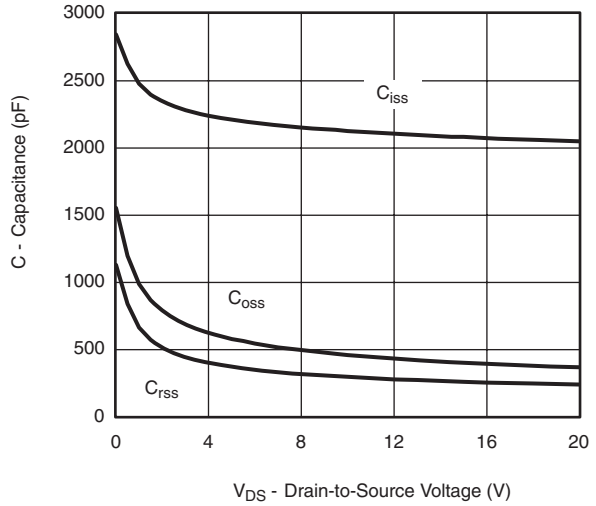
Output Characteristics



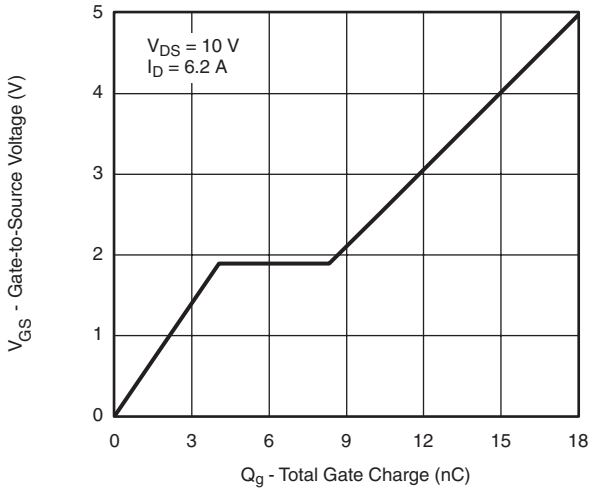
Transfer Characteristics



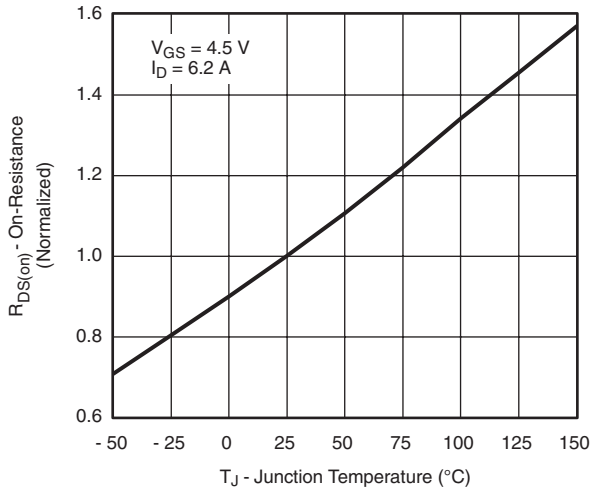
On-Resistance vs. Drain Current



Capacitance

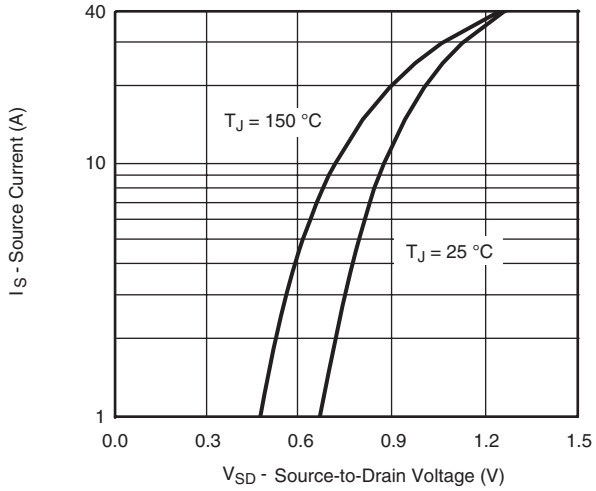


Gate Charge

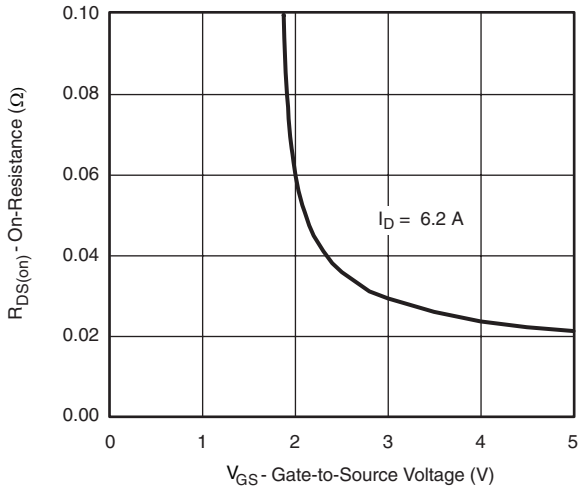


On-Resistance vs. Junction Temperature

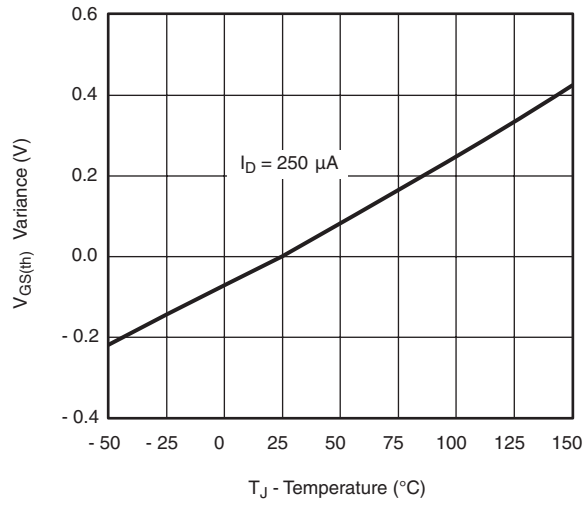
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



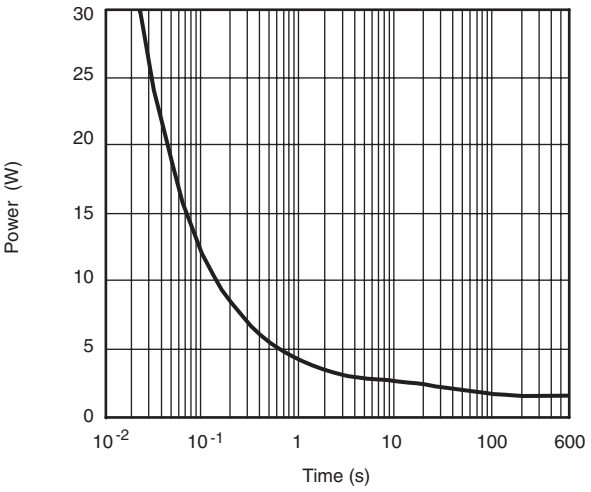
Source-Drain Diode Forward Voltage



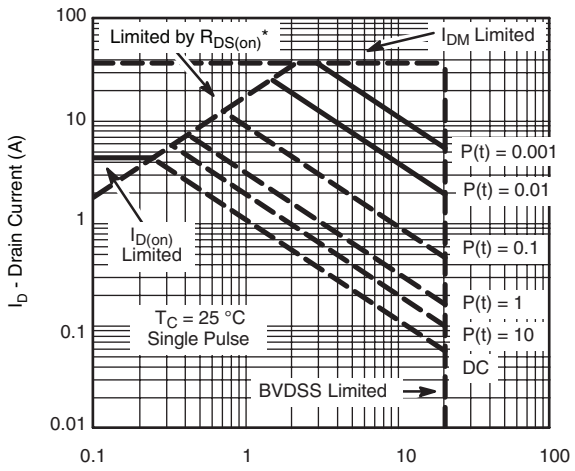
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



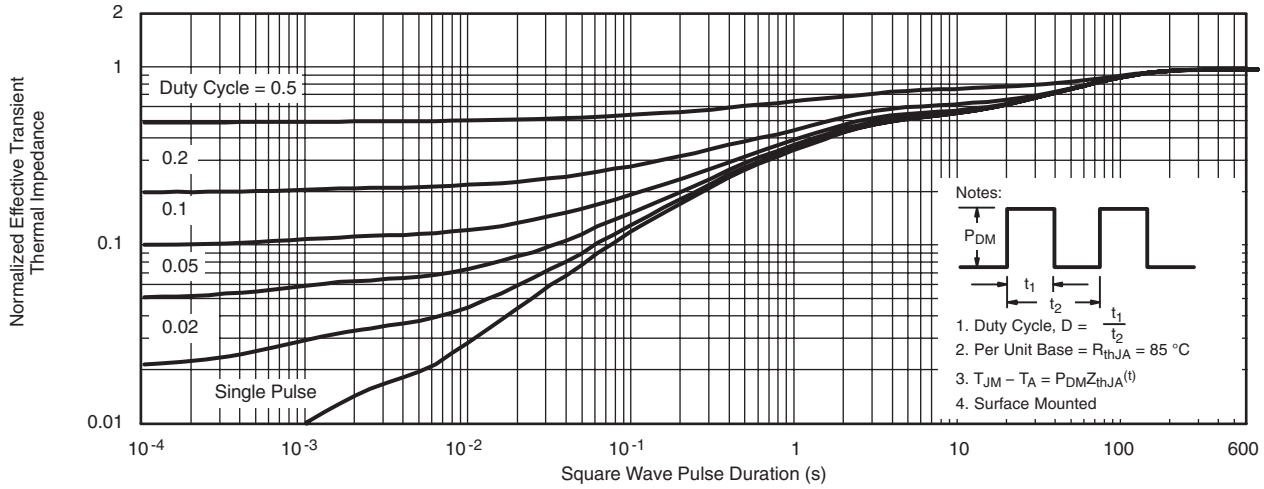
Single Pulse Power



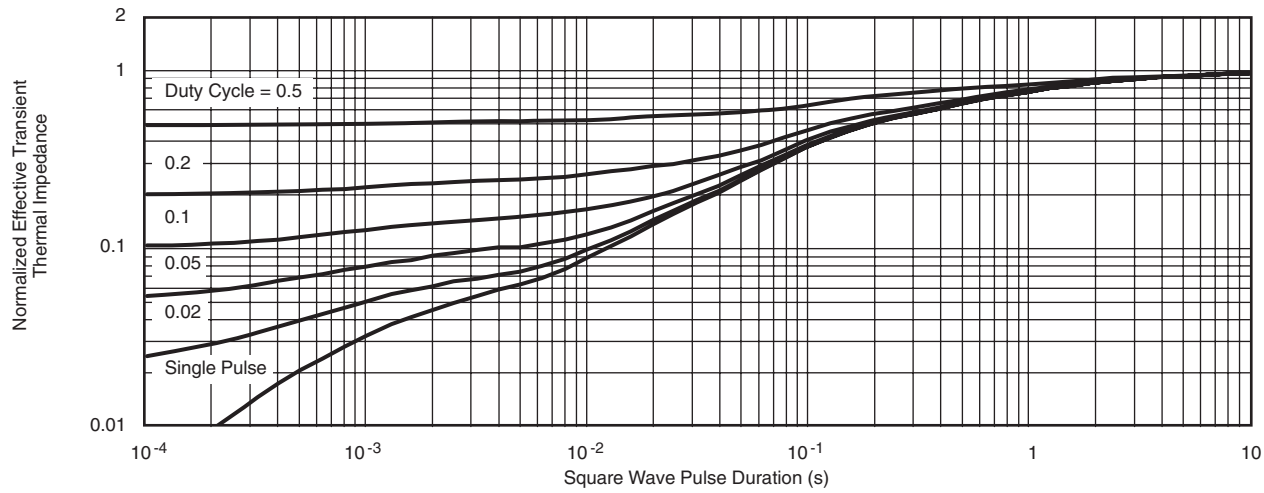
* V_{DS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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